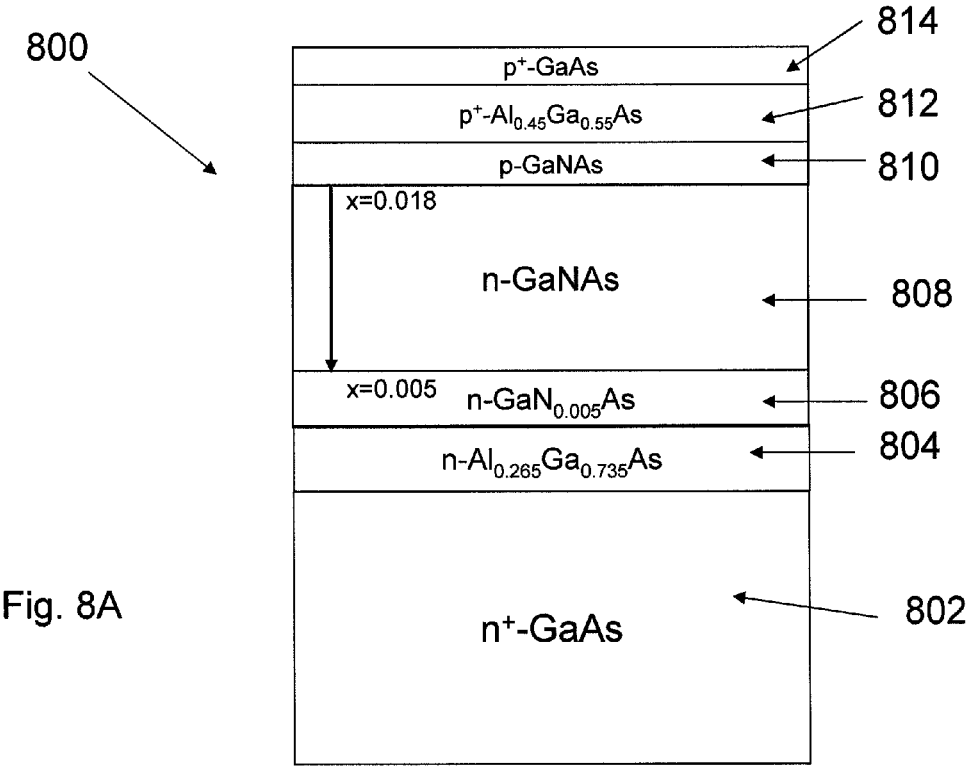
800
814
p+-GaAs
812
p+-Al0.45Ga0.55As
810
p-GaNAs
x=0.018
n-GaNAs
808
x=0.005
n-GaN0.005As
806
n-Al0.265Ga0.735As
804
n+-GaAs
802

Fig. 8A

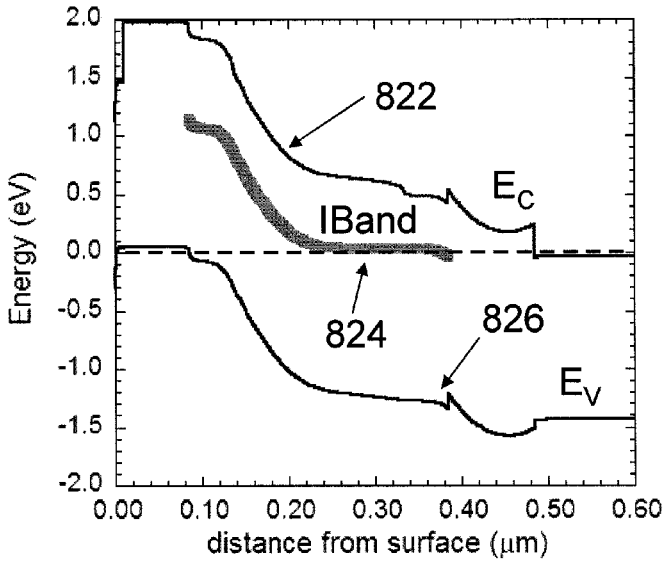
2.0
1.5
1.0
0.5
0.0
-0.5
-1.0
-1.5
-2.0
Energy (eV)
0.00
0.10
0.20
0.30
0.40
0.50
0.60
distance from surface (μm)
822
EC
IBand
824
826
EV

Fig. 8B